

Example- At 300 K for Si, find effective density of states # of charge carrier densities.

Constants

$$\begin{aligned} h &:= 6.62607015 \cdot 10^{-34} \text{ J-s} & m_0 &:= 9.1093837015 \cdot 10^{-31} \text{ kg} & T &:= 300 \text{ K} \\ k_B \text{ eV} &:= 8.617333 \cdot 10^{-5} \text{ eV/K} & k_B \text{ eV} \cdot T &= 0.025852 \text{ eV} \\ k_B &:= 1.380649 \cdot 10^{-23} \text{ J/K} & k_B \cdot T &= 4.14195 \times 10^{-21} \text{ J} & E_{g_Si} &:= 1.12 \text{ eV} \end{aligned}$$

From Table 4.1, the eff. electron & hole masses for Si $m_{ne} := 1.08 \cdot m_0$ $m_{pe} := 0.56 \cdot m_0$

Conduction band eff. density of states function (4.10)

$$N_c := 2 \cdot \left(\frac{2 \cdot \pi \cdot m_{ne} \cdot k_B \cdot T}{h^2} \right)^{\frac{3}{2}}$$

$$\boxed{N_c = 2.816 \times 10^{25} \text{ \#/m}^3} \quad \boxed{\frac{N_c}{100^3} = 2.816 \times 10^{19} \text{ \#/cm}^3}$$

From Table 4.1, $N_c = 2.8 \cdot 10^{19} \text{ \#/cm}^3$

Valence band eff. density of states function (4.18)

$$N_v := 2 \cdot \left(\frac{2 \cdot \pi \cdot m_{pe} \cdot k_B \cdot T}{h^2} \right)^{\frac{3}{2}}$$

$$\boxed{N_v = 1.052 \times 10^{25} \text{ \#/m}^3} \quad \boxed{\frac{N_v}{100^3} = 1.052 \times 10^{19} \text{ \#/cm}^3}$$

From Table 4.1, $N_v = 1.04 \cdot 10^{19} \text{ \#/cm}^3$

Assuming $E_c - E_F \sim 0.5 E_g$, the number of electrons is (4.11)

$$n_0 := N_c \cdot e^{-\left(\frac{0.5 \cdot E_{g_Si}}{k_B \text{ eV} \cdot T} \right)}$$

$$\boxed{n_0 = 1.102 \times 10^{16} \text{ \#/m}^3} \quad \boxed{\frac{n_0}{100^3} = 1.102 \times 10^{10} \text{ \#/cm}^3}$$

From Table 4.2, $n_0 = n_i = 1.5 \cdot 10^{19} \text{ \#/cm}^3$

Assuming $E_F - E_v \sim 0.5 E_g$, the number of holes is (4.19)

$$p_0 := N_v \cdot e^{-\left(\frac{0.5 \cdot E_{g_Si}}{k_B \text{ eV} \cdot T} \right)}$$

$$\boxed{p_0 = 4.114 \times 10^{15} \text{ \#/m}^3} \quad \boxed{\frac{p_0}{100^3} = 4.114 \times 10^9 \text{ \#/cm}^3}$$

From Table 4.2, $p_0 = n_i = 1.5 \cdot 10^{19} \text{ \#/cm}^3$